

AUTOMOTIVE CURRENT TRANSDUCER OPEN LOOP TECHNOLOGY HAH1DRW 900-S





Introduction

The HAH1DRW family is for the electronic measurement of DC, AC or pulsed currents in high power and low voltage automotive applications with galvanic separation between the primary circuit (high power) and the secondary circuit (electronic circuit).

The HAH1DRW family gives you the choice of having different current measuring ranges in the same housing.

Features

- · Ratiometric transducer
- Open Loop transducer using the Hall effect
- Low voltage application
- Unipolar + 5 V DC power supply
- Primary current measuring range ± 900 A
- Maximum RMS primary admissible current: defined by busbar to have T° < +150 °C
- Operating temperature range: -40 °C < T° < 125 °C
- Output voltage: full ratio-metric (in sensitivity and offset)

Advantages

- Excellent accuracy
- Very good linearity
- · Very low thermal offset drift
- · Very low thermal sensitivity drift
- Galvanic separation
- · High frequency bandwith
- Non intrusive solution.

Automotive applications

- Electrical Power Steering
- Starter Generators
- Converters
- Battery Management
- Motor drive application.

Principle of HAH1DRW Family

The open loop transducers uses a Hall effect integrated circuit. The magnetic flux density B, contributing to the rise of the Hall voltage, is generated by the primary current $I_{\rm p}$ to be measured. The current to be measured $I_{\rm p}$ is supplied by a current source i.e. battery or generator (Figure 1).

Within the linear region of the hysteresis cycle, *B* is proportional to:

 $B(I_{D}) = \text{constant (a)} \times I_{D}$

The Hall voltage is thus expressed by:

$$V_{H}$$
= (R_{H} /d) x I x constant (a) x I_{P}

Except for $I_{\rm p^{\rm s}}$ all terms of this equation are constant. Therefore:

 V_{\perp} = constant (b) x $I_{\scriptscriptstyle D}$

The measurement signal $V_{\rm H}$ amplified to supply the user output voltage or current.

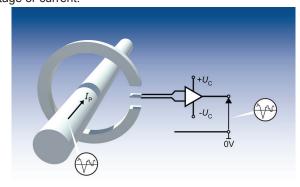
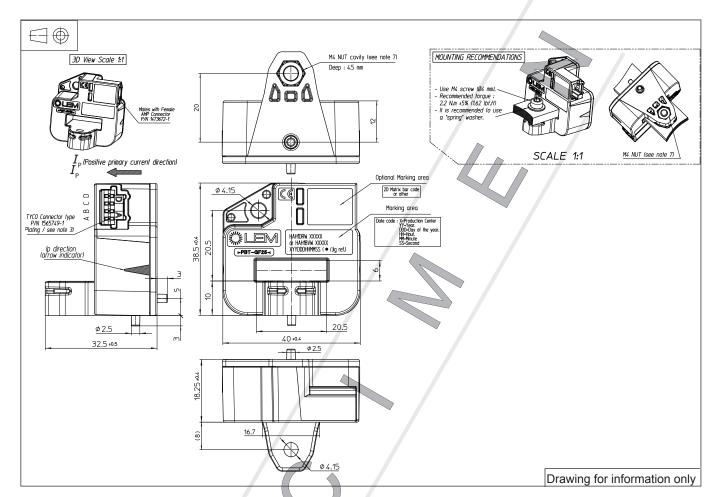


Fig. 1: Principle of the open loop transducer





Dimensions HAH1DRW 900-S (in mm)



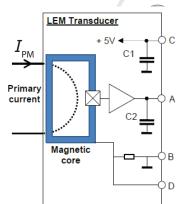
Mechanical characteristics

Plastic case
 Magnetic core
 Pins
 Brass tin plated
 Mass
 57 g ± 5 %

Mounting recommendation

Mating connector type TYCO P/N 1565749-1 type.Mates with AMP connector P/N 1473672-1

Assembly torque
 Soldering type
 N/A



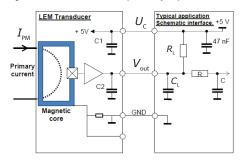
	IC	Hall sensor ASIC								
Þ	C1	Decoupling capacitor	47 nF							
-	C2	EMC protection capacitor	4.7 nF							
	Pin out									
4	Α	V								

	Pin out						
Α	V _{out}						
В	GND						
С	U _c (5 V)						
D	GND						

Remarks

- $I_{P} = \left(\frac{5}{U_{C}} \cdot V_{out} V_{O}\right) \cdot \frac{1}{G}$ with G in (V/A)
- V_{out} > V_o when I_p flows in the positive direction (see arrow on drawing).

System architecture (example)



 $C_{\rm L}$ < 2.2 nF EMC protection (optional)

RC Low pass filter (optional)

On board diagnostic

 $R_{\rm L}$ > 10 kΩ. Resistor for signal line diagnostic (optional)

V _{out}	Diagnostic
Open circuit	$V_{IN} = U_{C}$
Short GND	V _{IN} = 0 V



Absolute ratings (not operating)

Parameter	Symbol Unit		Specification		tion	Conditions
Parameter	Symbol	Unit	Min	Typical	Max	Conditions
Maximum supply voltage	$U_{\rm c}$	V	- 0.5		8	1)
Ambient storage temperature	Ts	°C	- 40		125	
Electrostatic discharge voltage (HBM)	U _{ESD}	kV			2	JESD22-A114-B
Maximum admissible vibration (random RMS)	γ	m∙s-²			96.6	10 to 2000 Hz, - 40 °C to 125 °C
RMS voltage for AC insulation test	U _d	kV			2.5	50 Hz, 1 min
Creepage distance	d _{Cp}	mm	5.2			
Clearance	d _{CI}	mm	4.9			
Comparative traking index	CTI	V	PLC	3 (175 V -	250 V)	
Maximum output Current	$I_{ m out}$	mA	- 10		10	
Maximum output Voltage	V _{out}	V	- 0.5		U _c + 0.5	
Maximum reverse current	I_{R}	mA		/	80	

Operating characteristics in nominal range ($I_{\rm PN}$)

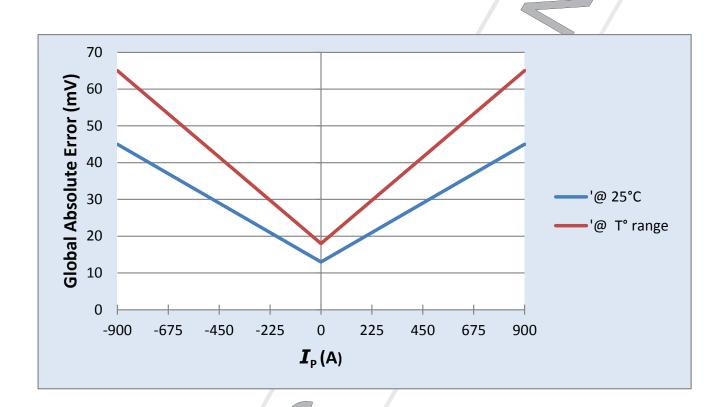
	Symbol	Unit	Specification		tion		
Parameter			Min	Typical	Max	Conditions	
Electrical Data							
Primary current, measuring range	$I_{\scriptscriptstyle{\mathrm{PM}}}$	А	- 900		900		
Primary nominal DC or RMS current	$I_{\scriptscriptstyle{PN}}$	Α	- 900		900		
Supply voltage	U _c	V	4.75	5	5.25		
Ambient operating temperature	T_{A}	°C	- 40		125		
Output voltage (Analog)	V_{out}	V	V _{out} = ((U _c /5) · (V _o	+ $G \cdot I_{P}$)		
Sensitivity	G	mV/A		2.222		@ T _A = 25 °C	
Offset voltage	$V_{\rm o}$	V		2.5			
Current consumption	$I_{ m c}$	mA		20	25	- 40 °C < T _A < 125 °C	
Load resistance	R _L	ΚΩ 🥎	10	/			
Output internal resistance	R _{out}	Ω		1	10		
		Perf	ormanc	e Data			
Ratiometricity error	ε,	%		± 0.5			
Sensitivity error	$\boldsymbol{\mathcal{E}}_{G}$	%		± 0.6		@ T _A = 25 °C	
Electrical offset current	$I_{\scriptscriptstyle{ extsf{OE}}}$	mV		± 3		@ $T_A = 25 ^{\circ}\text{C}$,@ $U_C = 5 ^{\circ}\text{V}$	
Magnetic offset voltage	V _{OM}	mV		± 2		@ $U_{\rm C}$ = 5 V, @ $T_{\rm A}$ = 25 °C	
Linearity error	$\epsilon_{\scriptscriptstyle \! \! \! \! \! \! \! \! \! \! \! \! \! \! \! \! \! \! \!$	%	- 1		1	% of full scale	
Average temperature coefficient of V_{OE}	TCV	mV/°C		± 0.04			
Average temperature coefficient of G	TCGAV	%/°C		± 0.02			
Step response time @ 70 %	t _r	μs		2	6	di/dt = 100 A / μs	
Frequency bandwidth	BW	kHz	40			@ - 3 dB	
Output voltage noise peak-peak	$V_{\text{no p-p}}$	mV			14	DC to 1 MHz	
Output RMS voltage noise	V _{no rms}	mV			2.2		
Phase shift	$\Delta oldsymbol{arphi}$	٥	- 4			DC to 1 KHz	

Notes: 1) Exceeding 6.5 V may temporarily reconfigure the device until next power on.





Global Absolute Error (mV) @ U_c = 5 V



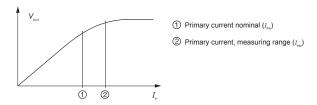
$I_{_{\mathrm{P}}}$ (A)	Accuracy @ 25 °C (mV)	Accuracy @ T ° range (mV)
- I _{PMAX}	45	65
0	13	18
I_{PMAX}	45	65





PERFORMANCES PARAMETERS DEFINITIONS

Primary current definition:



Definition of typical, minimum and maximum values:

Minimum and maximum values for specified limiting and safety conditions have to be understood as such as well as values shown in "typical" graphs. On the other hand, measured values are part of a statistical distribution that can be specified by an interval with upper and lower limits and a probability for measured values to lie within this interval. Unless otherwise stated (e.g. "100 % tested"), the LEM definition for such intervals designated with "min" and "max" is that the probability for values of samples to lie in this interval is 99.73 %. For a normal (Gaussian) distribution, this corresponds to an interval between -3 sigma and +3 sigma. If "typical" values are not obviously mean or average values, those values are defined to delimit intervals with a probability of 68.27 %, corresponding to an interval between -sigma and +sigma for a normal distribution. Typical, maximal and minimal values are determined during the initial characterization of a product.

Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear amplifier.

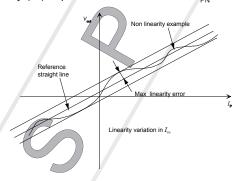
Magnetic offset:

The magnetic offset is the consequence of an over-current on the primary side. It's defined after an excursion of $I_{\rm PN}$.

Linearity:

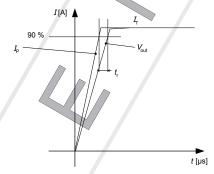
The maximum positive or negative discrepancy with a reference straight line $V_{\rm out}$ = $f(I_{\rm p})$.

Unit: linearity (%) expressed with full scale of I_{DN}



Response time (delay time) t_{\cdot} :

The time between the primary current signal $(I_{\rm PN})$ and the output signal reach at 90 % of its final value.



Sensitivity:

The Transducer's sensitivity G is the slope of the straight line $V_{\text{out}} = f(I_{\text{p}})$, it must establish the relation:

$$V_{\text{out}}(I_{\text{P}}) = U_{\text{C}}/5 (G \cdot I_{\text{P}} + V_{\text{O}})$$

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25 °C.

The offset variation $I_{\rm OT}$ is a maximum variation the offset in the temperature range:

$$I_{\text{OT}} = I_{\text{OE}} \max - I_{\text{OE}} \min$$

The Offset drift $TCI_{\rm OEAV}$ is the $I_{\rm OT}$ value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at 25 °C.

The sensitivity variation G_T is the maximum variation (in ppm or %) of the sensitivity in the temperature range:

 G_{T} = (Sensitivity max - Sensitivity min) / Sensitivity at 25 °C.

The sensitivity drift $TCG_{\rm AV}$ is the $G_{\rm T}$ value divided by the temperature range. Deeper and detailed info available is our LEM technical sales offices (www.lem.com).

Offset voltage @ $I_p = 0$ A:

The offset voltage is the output voltage when the primary current is null. The ideal value of $V_{\rm O}$ is $U_{\rm C}/2$ at $U_{\rm C}$ = 5 V. So, the difference of $V_{\rm O}$ - $U_{\rm C}/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis. Deeper and detailed info available is our LEM technical sales offices (www.lem.com).



Environmental test specifications:

Refer to LEM GROUP test plan laboratory CO.11.11.515.0 with "Tracking_Test Plan_Auto" sheet.

Name	Standard				
CHARACTERIZA	ATION @ 25 °C				
Sensitivity / Accuracy / Overall accuracy	LEM 98.20.00.574.0				
Offset / Electrical Offset / Magnetic Offset	LEM 98.20.00.573.0				
Linearity error	LEM 98.20.00.370.0				
Current Consumption	LEM 98.20.00.579.0				
CHARACTERIZATION	WITH T °C (initial)				
Sensitivity / Accuracy / Overall accuracy	LEM 98.20.00.574.0				
T °C variation of / Temperature Coefficient of G	LEM 98.20.00.574.0				
Offset / Electrical Offset / Magnetic Offset	LEM 98.20.00.573.0				
T °C variation of /Temperature Coefficient of Offset	LEM 98.20.00.573.0				
Linearity error	LEM 98.20.00.370.0				
Current Consumption	LEM 98.20.00.579.0				
ELECTRICAL TI	ESTS @ 25 °C				
Phase delay check	100H2 to 10kHz At 20 A peak				
Noise measurement	Sweep from DC to 1 MHz				
Response time di/dt	100 A/µs. / pulse = 700A				
dv/dt	2000 V/μs. V = 2000V				
Dielectric Withstand Voltage test	2500 VAC / 1 min / 50Hz				
Insulation Resistance test	500 \bigvee DC, time = 60 s R insulation >= 500 M Ω Minimum				
ENVIRONMENTAL TESTS (CLIMATIC)					
Thermal shock	IEC 60068-2-14 Na (01/2009)				
Steady state T°C Humidity bias life test	JESD 22-A101 (03/2009)				
MECHANICAL TESTS					
Vibration Random in T°C	IEC 60068-2-64 (02/2008)				
Shocks	IEC 60068-2-27 (02/2008)				
Free Fall (Device not packaged)	IEC 60068-2-31 §5.2: method 1 (05/2008)				
EMC					
Immunity to ElectroStatic Discharges (Handling of devices)	ISO 10605 (07/2008)				
Immunity to Conducted disturbances (BCI)	ISO 11452-4 (12/2011)				
Emission Radiated (ALSE)	CISPR 25 (03/2008)				

